

**Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

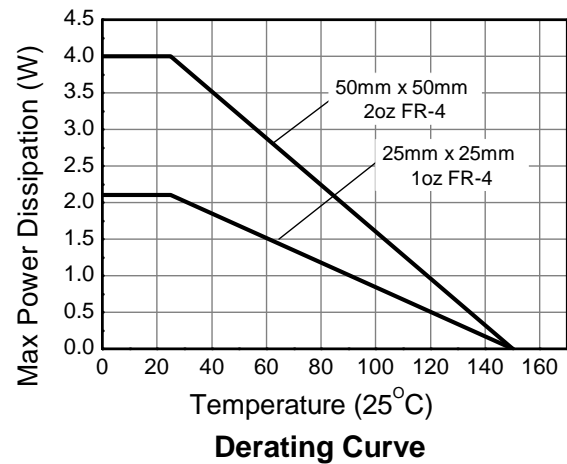
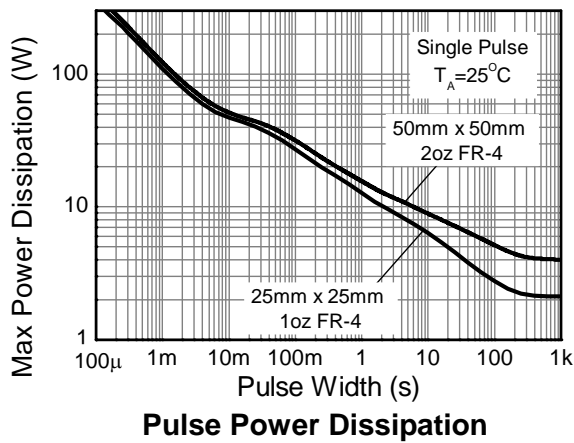
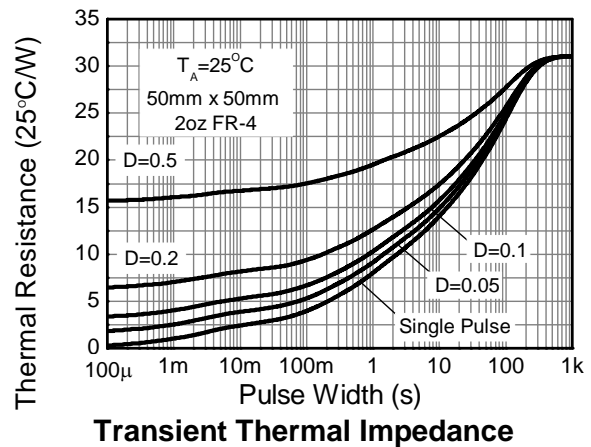
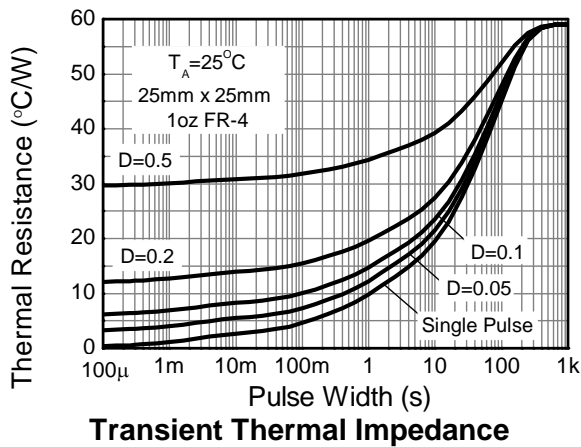
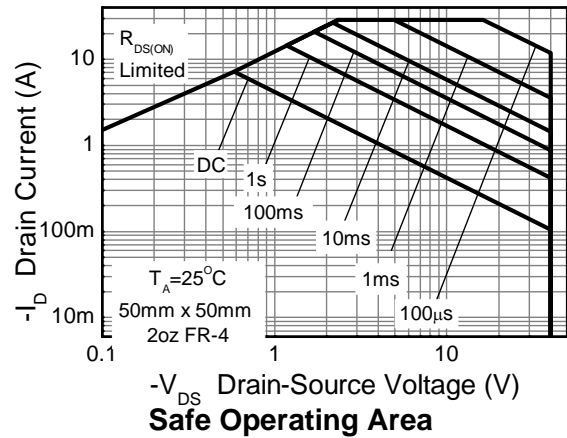
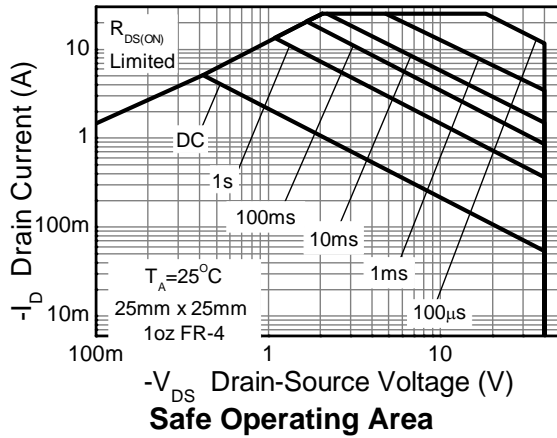
Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V <sub>DS</sub>	-40	V
Gate-Source Voltage	(Note 6)		V <sub>GS</sub>	±20	V
Single Pulsed Avalanche Energy	(Note 12)		E <sub>AS</sub>	50	mJ
Single Pulsed Avalanche Current	(Note 12)		I <sub>AS</sub>	-20.3	A
Continuous Drain Current	V <sub>GS</sub> = -10V	(Note 8)	I <sub>D</sub>	-10.5	A
		T <sub>A</sub> = +70°C (Note 8)		-8.40	
		(Note 7)		-7.2	
Pulsed Drain Current	V <sub>GS</sub> = -10V	(Note 9)	I <sub>DM</sub>	-28.9	A
Continuous Source Current (Body Diode)	(Note 8)		I <sub>S</sub>	-10.1	A
Pulsed Source Current (Body Diode)	(Note 8)		I <sub>SM</sub>	-28.9	A

**Thermal Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Power Dissipation Linear Derating Factor	(Note 7)	P <sub>D</sub>	4.18	W mW/°C
			33.4	
	(Note 8)		8.9	
	(Note 10)		71.4	
Thermal Resistance, Junction to Ambient	(Note 7)	R <sub>θJA</sub>	2.14	°C/W
	(Note 8)		17.1	
	(Note 10)		29.9	
Thermal Resistance, Junction to Lead	(Note 8)	R <sub>θJL</sub>	14.0	°C/W
	(Note 10)		58.4	
	(Note 11)		2.46	
Operating and Storage Temperature Range		T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

- Notes:
- AEC-Q101 V<sub>GS</sub> maximum is ±16V.
  - For a device surface mounted on 50mm x 50mm x 1.6mm FR-4 PCB with high coverage of single sided 2oz copper, in still air conditions; the device is measured when operating in a steady-state condition.
  - Same as note 7, except the device is measured at t ≤ 10s.
  - Same as note 7, except the device is pulsed with D = 0.02 and pulse width 300μs. The pulse current is limited by the maximum junction temperature.
  - For a device surface mounted on 25mm x 25mm x 1.6mm FR-4 PCB with high coverage of single sided 1oz copper, in still air conditions; the device is measured when operating in a steady-state condition.
  - Thermal resistance from junction to solder-point (at the end of the drain lead).
  - UIS in production with L = 100μH, V<sub>DD</sub> = -40V.

## Thermal Characteristics

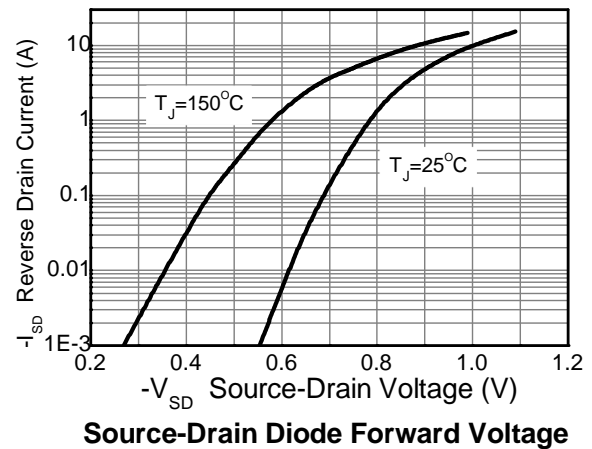
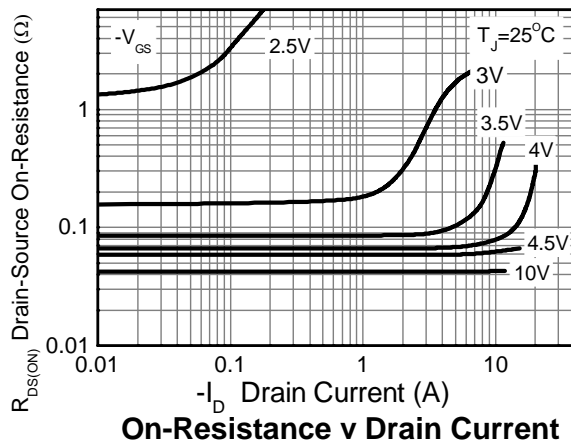
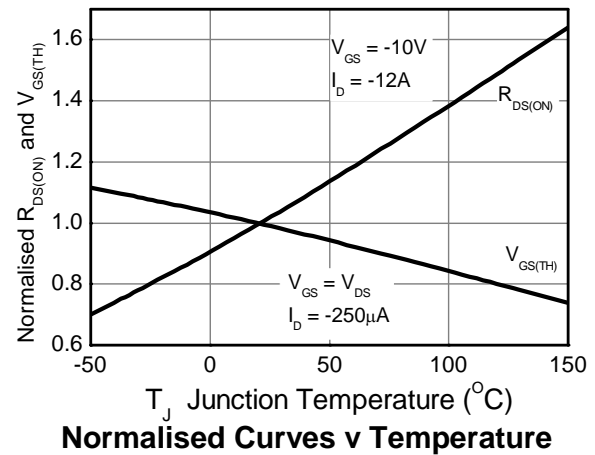
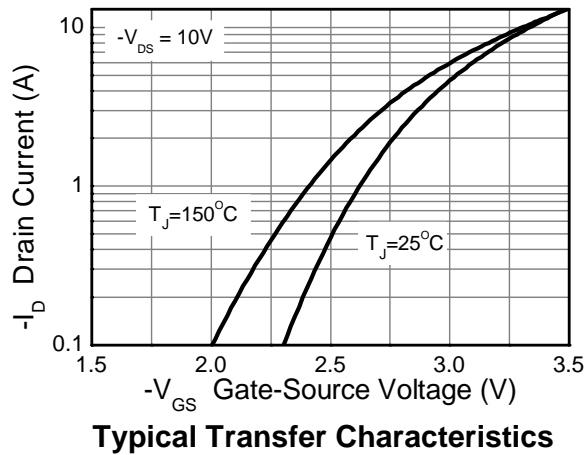
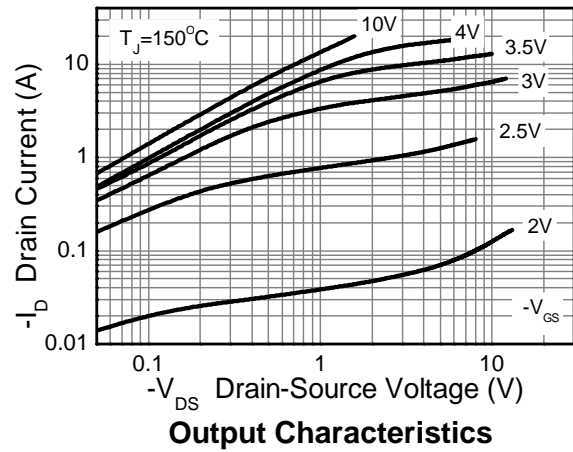
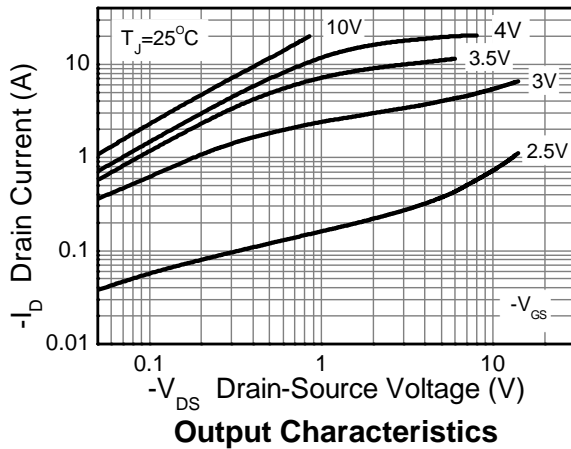


**Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

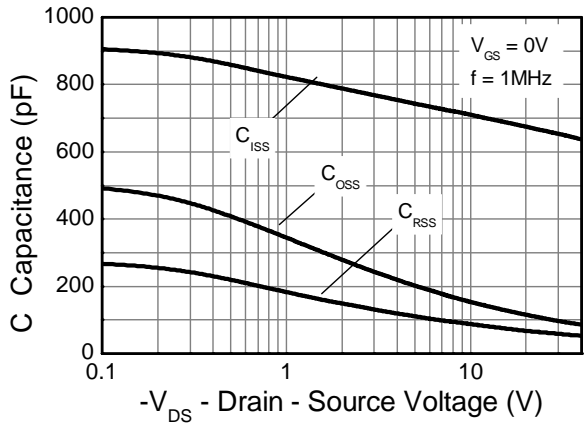
Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition	
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	-40	—	—	V	I <sub>D</sub> = -250μA, V <sub>GS</sub> = 0V	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	—	—	-0.5	μA	V <sub>DS</sub> = -40V, V <sub>GS</sub> = 0V	
Gate-Source Leakage	I <sub>GSS</sub>	—	—	±100	nA	V <sub>GS</sub> = ±20V, V <sub>DS</sub> = 0V	
ON CHARACTERISTICS							
Gate Threshold Voltage	V <sub>GS(TH)</sub>	-1.0	—	-3.0	V	I <sub>D</sub> = -250μA, V <sub>DS</sub> = V <sub>GS</sub>	
Static Drain-Source On-Resistance (Note 14)	R <sub>DS(ON)</sub>	—	0.041	0.051	Ω	V <sub>GS</sub> = -10V, I <sub>D</sub> = -12A	
			0.059	0.085		V <sub>GS</sub> = -4.5V, I <sub>D</sub> = -8A	
Forward Transconductance (Notes 13 & 14)	g <sub>fs</sub>	—	16.6	—	s	V <sub>DS</sub> = -15V, I <sub>D</sub> = -12A	
Diode Forward Voltage (Note 13)	V <sub>SD</sub>	—	-0.98	-1.2	V	I <sub>S</sub> = -12A, V <sub>GS</sub> = 0V	
Reverse Recovery Time (Note 14)	t <sub>rr</sub>	—	138	—	ns	I <sub>S</sub> = -12A, di/dt = 100A/μs	
Reverse Recovery Charge (Note 13)	Q <sub>rr</sub>	—	841	—	nC		
DYNAMIC CHARACTERISTICS (Note 14)							
Input Capacitance	C <sub>ISS</sub>	—	674	—	pF	V <sub>DS</sub> = -20V, V <sub>GS</sub> = 0V f = 1MHz	
Output Capacitance	C <sub>OSS</sub>	—	115	—	pF		
Reverse Transfer Capacitance	C <sub>RSS</sub>	—	67.7	—	pF		
Total Gate Charge (Note 15)	Q <sub>G</sub>	—	7.0	—	nC	V <sub>GS</sub> = -4.5V	V <sub>DS</sub> = -20V I <sub>D</sub> = -12A
Total Gate Charge (Note 15)	Q <sub>G</sub>	—	14	—	nC	V <sub>GS</sub> = -10V	
Gate-Source Charge (Note 15)	Q <sub>GS</sub>	—	2.2	—	nC		
Gate-Drain Charge (Note 15)	Q <sub>GD</sub>	—	3.7	—	nC		
Turn-On Delay Time (Note 15)	t <sub>d(on)</sub>	—	2.3	—	ns	V <sub>DD</sub> = -20V, V <sub>GS</sub> = -10V I <sub>D</sub> = -12A, R <sub>G</sub> ≅ 6.0Ω	
Turn-On Rise Time (Note 15)	t <sub>r</sub>	—	14.1	—	ns		
Turn-Off Delay Time (Note 15)	t <sub>d(off)</sub>	—	25.1	—	ns		
Turn-Off Fall Time (Note 15)	t <sub>f</sub>	—	14.3	—	ns		

- Notes:
- 13. Measured under pulsed conditions. Pulse width ≤ 300μs; duty cycle ≤ 2%.
  - 14. For design aid only, not subject to production testing.
  - 15. Switching characteristics are independent of operating junction temperatures.

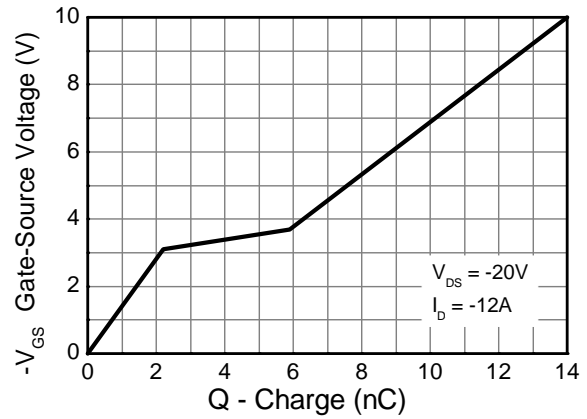
## Typical Characteristics



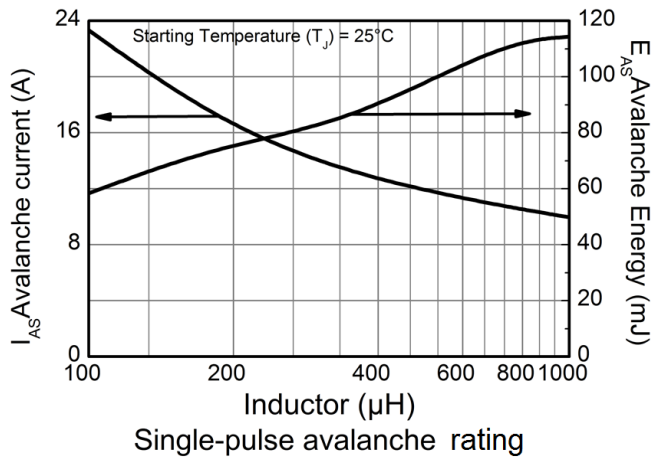
**Typical Characteristics (Cont.)**



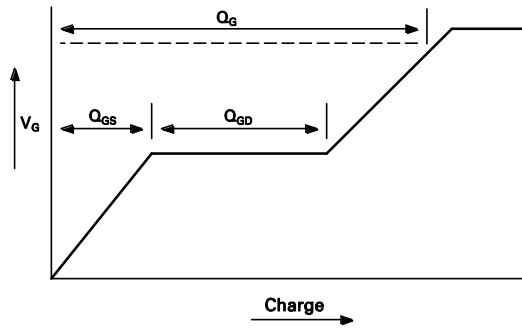
**Capacitance v Drain-Source Voltage**



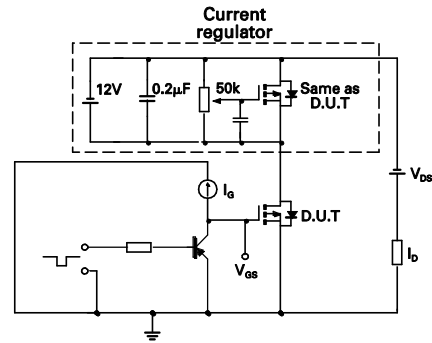
**Gate-Source Voltage v Gate Charge**



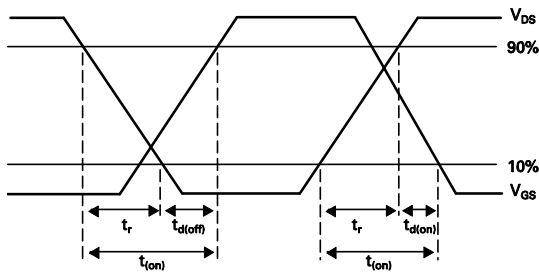
## Test Circuits



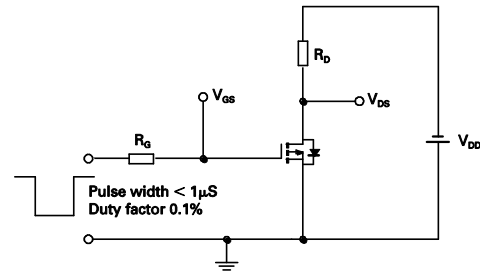
**Basic gate charge waveform**



**Gate charge test circuit**



**Switching time waveforms**

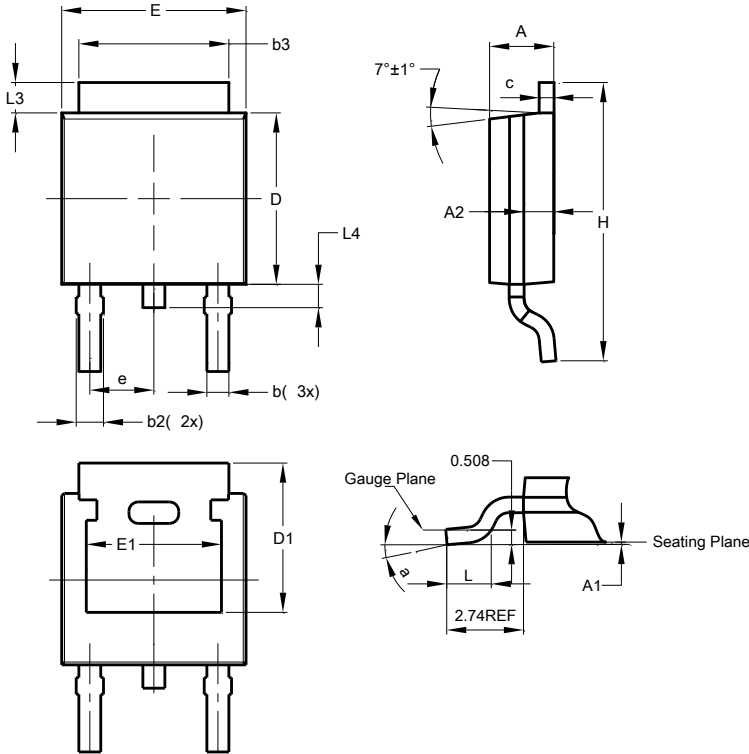


**Switching time test circuit**

## Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

### TO252 (DPAK)

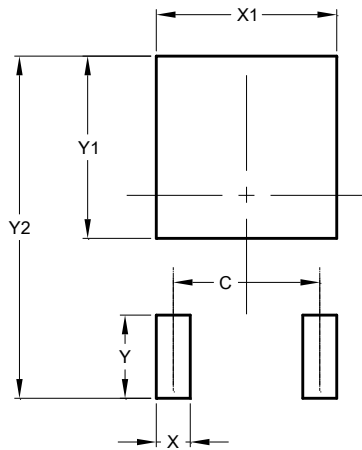


TO252 (DPAK)			
Dim	Min	Max	Typ
A	2.19	2.39	2.29
A1	0.00	0.13	0.08
A2	0.97	1.17	1.07
b	0.64	0.88	0.783
b2	0.76	1.14	0.95
b3	5.21	5.46	5.33
c	0.45	0.58	0.531
D	6.00	6.20	6.10
D1	5.21	-	-
e	-	-	2.286
E	6.45	6.70	6.58
E1	4.32	-	-
H	9.40	10.41	9.91
L	1.40	1.78	1.59
L3	0.88	1.27	1.08
L4	0.64	1.02	0.83
a	0°	10°	-
All Dimensions in mm			

## Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

### TO252 (DPAK)



Dimensions	Value (in mm)
C	4.572
X	1.060
X1	5.632
Y	2.600
Y1	5.700
Y2	10.700

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